Designer's™ Data Sheet Axial Lead Rectifiers

... employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features chrome barrier metal, epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

- Extremely Low v_F
- Low Power Loss/High Efficiency
- Low Stored Charge, Majority Carrier Conduction

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.1 gram (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 220°C Max. for 10 Seconds, 1/16″ from case
- Shipped in plastic bags, 5,000 per bag
- Available Tape and Reeled, 1500 per reel, by adding a "RL" suffix to the part number
- Polarity: Cathode indicated by Polarity Band
- Marking: 1N5820, 1N5821, 1N5822

SCHOTTKY BARRIER RECTIFIERS 3.0 AMPERES 20, 30, 40 VOLTS

1N5820

1N5821 1N5822

1N5820 and 1N5822 are

Motorola Preferred Devices



MAXIMUM RATINGS

Rating	Symbol	1N5820	1N5821	1N5822	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	20	30	40	V
Non-Repetitive Peak Reverse Voltage	VRSM	24	36	48	V
RMS Reverse Voltage	VR(RMS)	14	21	28	V
Average Rectified Forward Current (2) $V_{R(equiv)} \leq 0.2 V_{R(dc)}, T_{L} = 95^{\circ}C$ $(R_{\theta}JA = 28^{\circ}C/W, P.C. Board Mounting, see Note 2)$	IO	•	3.0	*	A
Ambient Temperature Rated $V_R(d_C)$, $P_F(AV) = 0$ $R_{\theta JA} = 28^{\circ}C/W$	ТА	90	85	80	°C
Non–Repetitive Peak Surge Current (Surge applied at rated load conditions, half wave, single phase 60 Hz, $T_L = 75^{\circ}C$)	IFSM - 80 (for one of) (for one cyc	le) ——►	A
Operating and Storage Junction Temperature Range (Reverse Voltage applied)	TJ, Tstg	<u> </u>	65 to +12	5	°C
Peak Operating Junction Temperature (Forward Current applied)	T _{J(pk)}	<	<u> </u>		°C

*THERMAL CHARACTERISTICS (Note 2)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	28	°C/W

(1) Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle = 2.0%.

(2) Lead Temperature reference is cathode lead 1/32" from case.

* Indicates JEDEC Registered Data for 1N5820-22.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

Preferred devices are Motorola recommended choices for future use and best overall value.

Rev 2



*ELECTRICAL CHARACTERISTICS (T_L = 25°C unless otherwise noted) (2)

Characteristic	Symbol	1N5820	1N5821	1N5822	Unit
Maximum Instantaneous Forward Voltage (1) (iF = 1.0 Amp) (iF = 3.0 Amp) (iF = 9.4 Amp)	VF	0.370 0.475 0.850	0.380 0.500 0.900	0.390 0.525 0.950	V
Maximum Instantaneous Reverse Current @ Rated dc Voltage (1) $T_L = 25^{\circ}C$ $T_L = 100^{\circ}C$	iR	2.0 20	2.0 20	2.0 20	mA

(1) Pulse Test: Pulse Width = $300 \,\mu$ s, Duty Cycle = 2.0%.

(2) Lead Temperature reference is cathode lead 1/32" from case.

* Indicates JEDEC Registered Data for 1N5820-22.

NOTE 1 — DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 0.1 V_{RWM} . Proper derating may be accomplished by use of equation (1).

 $\begin{array}{l} T_A(max) = T_J(max) - R_{\theta J}A^P F(AV) - R_{\theta J}A^P R(AV) \quad (1) \\ \text{where } T_A(max) = \text{Maximum allowable ambient temperature} \\ T_J(max) = \text{Maximum allowable junction temperature} \\ (125^{\circ}C \text{ or the temperature at which thermal} \\ runaway occurs, whichever is lowest) \end{array}$

 $P_{F(AV)}$ = Average forward power dissipation $P_{R(AV)}$ = Average reverse power dissipation

 $R_{\theta JA} =$ Junction-to-ambient thermal resistance

Figures 1, 2, and 3 permit easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figures solve for a reference temperature as determined by equation (2).

$$T_{R} = T_{J(max)} - R_{\theta JA} P_{R}(AV)$$
(2)

Substituting equation (2) into equation (1) yields:

$$A(\max) = R - R_{\theta} JA^{\rho} F(AV)$$
(3)

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where $T_J = 125^{\circ}C$, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figures 1, 2, and 3 as a difference in the rate of change of the slope in the vicinity of 115°C.

The data of Figures 1, 2, and 3 is based upon dc conditions. For use in common rectifier circuits, Table 1 indicates suggested factors for an equivalent dc voltage to use for conservative design, that is:

$$V_{R(equiv)} = V(FM) \times F$$
 (4)

The factor F is derived by considering the properties of the various rectifier circuits and the reverse characteristics of Schottky diodes.

EXAMPLE: Find T_{A(max)} for 1N5821 operated in a 12–volt dc supply using a bridge circuit with capacitive filter such that I_{DC} = 2.0 A (I_{F(AV)} = 1.0 A), I_(FM)/I_(AV) = 10, Input Voltage = 10 V_(rms), R_{θ JA} = 40°C/W.

Step 1. Find $V_{R(equiv)}$. Read F = 0.65 from Table 1, $\therefore V_{R(equiv)} = (1.41) (10) (0.65) = 9.2 V.$

Step 2. Find T_R from Figure 2. Read T_R = 108°C @ V_R = 9.2 V and R_{θ JA} = 40°C/W.

Step 3. Find $P_{F(AV)}$ from Figure 6. **Read $P_{F(AV)} = 0.85$ W

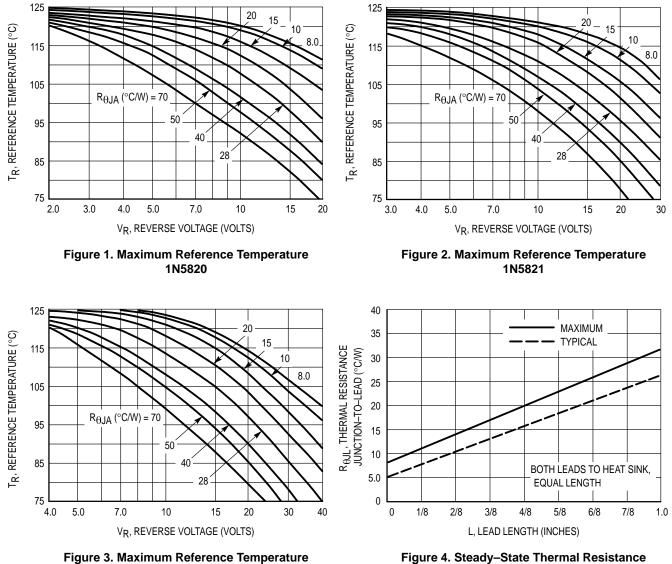
Step 4. Find $T_{A(max)}$ from equation (3). $T_{A(max)} = 108 - (0.85) (40) = 74^{\circ}C.$

**Values given are for the 1N5821. Power is slightly lower for the 1N5820 because of its lower forward voltage, and higher for the 1N5822. Variations will be similar for the MBR–prefix devices, using PF(AV) from Figure 7.

Table 1. Values for Factor F

Circuit	Half	Wave	Full Wave, Bridge		Full Wave, Center Tapped*†	
Load	Resistive	Capacitive*	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.5	1.3	0.5	0.65	1.0	1.3
Square Wave	0.75	1.5	0.75	0.75	1.5	1.5

*Note that $V_{R(PK)} \approx 2.0 V_{in(PK)}$. †Use line to center tap voltage for V_{in} .



1N5822

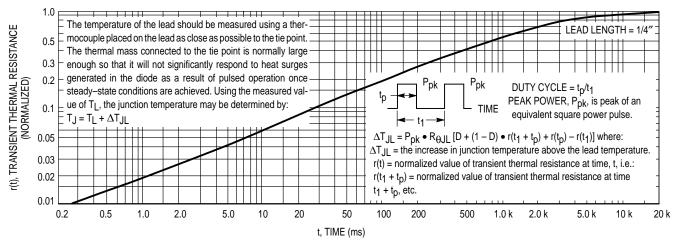


Figure 5. Thermal Response

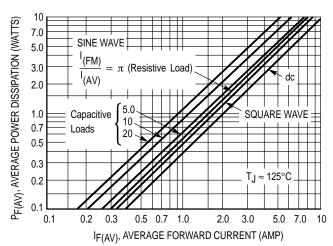
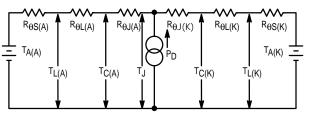


Figure 6. Forward Power Dissipation 1N5820–22

NOTE 3 — APPROXIMATE THERMAL CIRCUIT MODEL



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heat sink. Terms in the model signify:

T_A = Ambient Temperature T_C = Case Temperature T_J = Junction Temperature

- T_I = Lead Temperature $R_{\theta S}^{-}$ = Thermal Resistance, Heat Sink to Ambient
- $R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink

 $R_{\theta J}$ = Thermal Resistance, Junction to Case

 P_D = Total Power Dissipation = $P_F + P_R$

PF = Forward Power Dissipation

PR = Reverse Power Dissipation

(Subscripts (A) and (K) refer to anode and cathode sides, respectively.) Values for thermal resistance components are:

 $R_{\Theta I} = 42^{\circ}C/W/in$ typically and $48^{\circ}C/W/in$ maximum

 $R_{\theta J} = 10^{\circ}$ C/W typically and 16°C/W maximum

The maximum lead temperature may be found as follows:

 $\begin{array}{l} \mathsf{T}_{L} = \mathsf{T}_{J(max)} \ - \ \Delta \ \mathsf{T}_{JL} \\ \text{where} \ \Delta \ \mathsf{T}_{JL} \approx \ \mathsf{R}_{\theta JL} \cdot \mathsf{P}_{D} \end{array}$

Mounting Method 3 Mounting Method 1 P.C. Board with P.C. Board where available 2-1/2" x 2-1/2" copper surface is small. copper surface. L = 1/2'**Mounting Method 2** BOARD GROUND PLANE VECTOR PUSH-IN **TERMINALS T-28**

NOTE 2 — MOUNTING DATA

Data shown for thermal resistance junction-to-ambient (R_{0.IA}) for the mountings shown is to be used as typical guideline values for preliminary engineering, or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $R_{\theta, JA}$ IN STILL AIR

			00/1		
Mounting	Lead Length, L (in)				
Method	1/8	1/4	1/2	3/4	$R_{\theta JA}$
1	50	51	53	55	°C/W
2	58	59	61	63	°C/W
3	28				°C/W

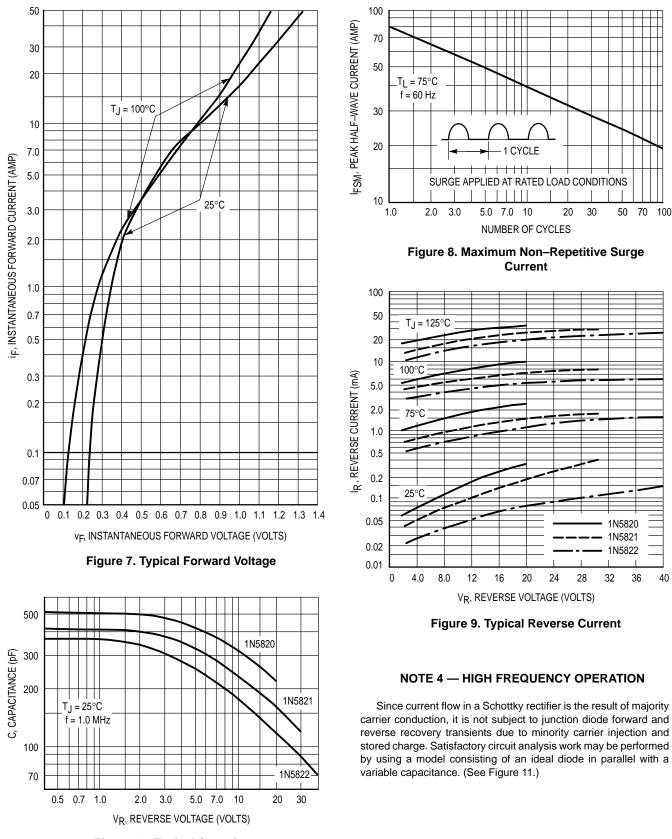
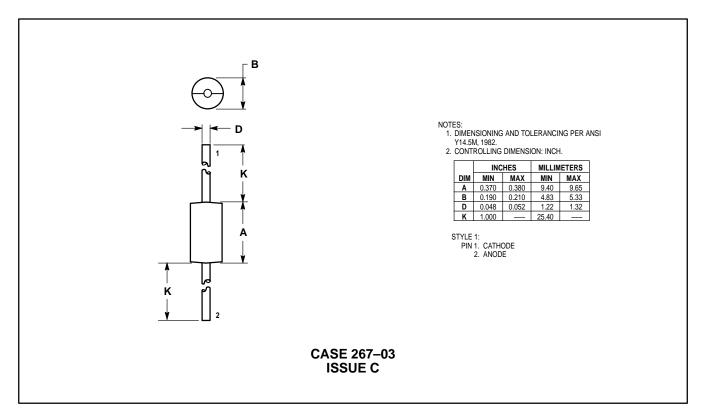


Figure 10. Typical Capacitance

PACKAGE DIMENSIONS



Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights or the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and **()** are registered trademarks of Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado 80217. 303–675–2140 or 1–800–441–2447

 \Diamond

JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, 6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 81–3–3521–8315

Mfax is a trademark of Motorola. Inc.

Mfax™: RMFAX0@email.sps.mot.com – TOUCHTONE 602–244–6609 INTERNET: http://Design–NET.com ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.